

IN THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. (Original) An electronic component comprising:
a conductive pattern provided on an insulating substrate;
a metal film formed by a plating method on a surface of the conductive pattern; and
a metal oxide layer formed by oxidizing the metal film and disposed on the surface of the conductive pattern.

2. (Currently Amended) [[An]] The electronic component comprising: as defined in claim 1, wherein
~~a conductive pattern provided on an insulating substrate;~~
~~[[a]] the metal film is formed by a plating method on a surface of the conductive pattern and a space between electrodes of the pattern on the substrate[[:]]; and~~
~~a metal oxide layer formed by oxidizing the metal film and disposed on the surface of the conductive pattern and also on the space between the electrodes of the pattern on the substrate.~~

3. (Currently Amended) [[An]] The electronic component comprising: as defined in claim 1, wherein
~~a conductive pattern provided on an insulating substrate;~~
~~[[a]] the metal film is formed by a plating method on a surface of the substrate, where the conductive pattern is provided; and~~
~~a metal oxide layer formed by oxidizing the metal film and disposed on the surface of the substrate.~~

4. (Currently Amended) The electronic component as defined in [[one of]]
claim 1[[, 2 or 3]], wherein the substrate uses a ceramic substrate.

5. (Currently Amended) The electronic component as defined in [[one of]]
claim 1[[, 2 or 3]], wherein the substrate uses a glass-ceramic substrate.

6. (Currently Amended) The electronic component as defined in [[one of]]
claim 1[[, 2 or 3]], wherein the substrate uses an organic substrate.

7. (Currently Amended) The electronic component as defined in [[one of]]
claim 1[[, 2 or 3]], wherein the conductive pattern uses electrode material including at least Ag.

8. (Original) The electronic component of claim 7, wherein the electrode
material includes one material selected from the group consisting of Ag, Ag – Pt, and Ag – Pd.

9. (Currently Amended) The electronic component as defined in [[one of]]
claim 1[[, 2 or 3]], wherein the metal oxide layer includes one material selected from the group
consisting of NiO, ZnO, and CuO.

10. (Currently Amended) The electronic component as defined in [[one of]]
claim [[1, 2 or 3]] 9, wherein the metal oxide layer has a thickness ranging from 0.5μm to 5μm.

11. (Cancelled)

12. (Currently Amended) The electronic component as defined in [[one of]]
claim 1, [[2 or 3,]] wherein a part of the conductive pattern is exposed outward.

13. (Currently Amended) The electronic component as defined in [[one of]] claim 2 [[or 3]], wherein a part of the conductive pattern and a part of the substrate are exposed outward.

14. (Currently Amended) The electronic component as defined in claim 3, wherein a part of the conductive pattern and a part of the substrate are exposed outward. A method of manufacturing an electronic component, the method comprising the steps of: forming a conductive pattern on an insulating substrate; forming a metal film by a plating method on a surface of the conductive pattern; and forming a metal oxide layer on the surface of the conductive pattern by oxidizing the metal film.

15. (Currently Amended) A method of manufacturing an electronic component, the method comprising the steps of: forming a conductive pattern on an insulating substrate; forming a metal film by a plating method on a surface of the conductive pattern; and on a space between electrodes of the pattern on the substrate; and forming a metal oxide layer by oxidizing the metal film on the surface of the conductive pattern; forming a metal oxide layer on the surface of the conductive pattern by oxidizing the metal film and on the space between electrodes of the pattern on the substrate.

16. (Currently Amended) [[A]] The method of manufacturing an electronic component as defined in claim 15, wherein the method comprising comprises the steps of: forming a conductive pattern on an insulating substrate; forming [[a]] the metal film by a plating method on a surface of the conductive pattern and on a space between electrodes of the pattern on the substrate, where the conductive pattern is formed; and

~~forming a metal oxide layer by oxidizing the metal film on the surface of the substrate.~~

17. (Currently Amended) The method of manufacturing an electronic component as defined in [[one of]] claim 14[[, 15 or 16]], wherein the method comprises the steps of:

forming the metal film by a plating method on a surface of the substrate, where the conductive pattern is formed uses an electroless plating method.

18. (Currently Amended) The method as defined in one of claim [[14,]] 15 [[or 16]], wherein the plating method uses an electroless plating method oxidizing is done by a heat treatment.

19. (Currently Amended) The method as defined in [[one of]] claim [[14,]] 15 [[or 16,]] wherein the plating method uses an electroless plating method oxidizing is done by a heat treatment.

20. (Currently Amended) The method as defined in claim 19, wherein the heat treatment is carried out at a temperature not higher than a melting point of the conductive pattern. A method of manufacturing an electronic component, the method comprising the steps of:

~~forming a conductive pattern on an insulating substrate;~~
~~forming a nickel film by a plating method at least on a surface of the conductive pattern;~~
~~forming nickel oxide as a metal oxide layer at least on the surface of the conductive pattern by providing the nickel film with an oxidation heat treatment at a temperature between 850°C and a melting point of electrode material forming the conductive pattern.~~

21. (New) A method of manufacturing an electronic component, the method comprising the steps of:

forming a conductive pattern on an insulating substrate;

forming a nickel film by a plating method at least on a surface of the conductive pattern;
forming nickel oxide as a metal oxide layer at least on the surface of the conductive pattern by providing the nickel film with an oxidation heat treatment at a temperature between 850°C and a melting point of electrode material forming the conductive pattern.